

Marwan Bou Sanayeh

List of Publications by Year in descending order

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13
papers

176
citations

1163117

8
h-index

1372567

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13
all docs

13
docs citations

13
times ranked

121
citing authors

#	ARTICLE	IF	CITATIONS
1	Impedance Characteristics and Chip-Parasitics Extraction of High-Performance VCSELs. IEEE Journal of Quantum Electronics, 2020, 56, 1-11.	1.9	10
2	Equivalent Circuit Model of High-Performance VCSELs. Photonics, 2020, 7, 13.	2.0	4
3	Extrinsic dynamics and Equivalent Circuit Modeling of High-Speed VCSELs. , 2019, , .		0
4	Small-Signal Analysis of High-Performance VCSELs. IEEE Photonics Journal, 2019, 11, 1-12.	2.0	11
5	Influence of resonator length on catastrophic optical damage in high-power AlGaInP broad-area lasers. Proceedings of SPIE, 2017, , .	0.8	0
6	Small-signal analysis of ultra-high-speed 30 GHz VCSELs using an advanced multi-mode approach. , 2017, , .		0
7	Polarization-stable vertical-cavity surface-emitting lasers with inverted grating relief for use in microscale atomic clocks. Applied Physics Letters, 2012, 101, .	3.3	24
8	Polarization Control and Dynamic Properties of VCSELs for MEMS Atomic Clock Applications. IEEE Photonics Technology Letters, 2011, 23, 1049-1051.	2.5	27
9	Pressure and temperature tuning of InGaP/AlGaInP laser diodes from red to yellow. Physica Status Solidi (B): Basic Research, 2009, 246, 508-511.	1.5	5
10	Defect investigation and temperature analysis of high-power AlGaInP laser diodes during catastrophic optical damage. Journal of Materials Science: Materials in Electronics, 2008, 19, 155-159.	2.2	8
11	Real-time thermal imaging of catastrophic optical damage in red-emitting high-power diode lasers. Applied Physics Letters, 2008, 92, 103514.	3.3	27
12	Infrared emission from the substrate of GaAs-based semiconductor lasers. Applied Physics Letters, 2008, 93, .	3.3	11
13	Investigation of dark line defects induced by catastrophic optical damage in broad-area AlGaInP laser diodes. Applied Physics Letters, 2006, 89, 101111.	3.3	49